

Abstract

Creation of dielectrically insulating SOI- technological trenches comprising rounded edges for allowing higher voltages

The aim of the invention is to integrate low-voltage logic elements and high-voltage power elements in one and the same silicon circuit. Said aim is achieved by dielectrically chip regions having different potentials from each other with the aid of isolation trenches (10). In order to prevent voltage rises at sharp edges on the bottom of the isolation trenches, said edges are rounded in a simple process, part of the insulating layer (2) being isotropically etched.

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